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(54) **SYSTEM AND METHOD FOR PLASMA PROCESSING**

(71) Applicant: **Tokyo Electron Limited**, Tokyo (JP)

(72) Inventors: **Merritt Funk**, Austin, TX (US); **Barton Lane**, Austin, TX (US); **Yohei Yamazawa**, Tokyo (JP)

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(57) **ABSTRACT**

An apparatus for plasma processing includes an RF power source and a set of resonating structures coupled to the RF power source. The resonating structures include a first region and a second region adjacent to the second region. The first region includes a first antenna and a first coupling circuit, the first coupling circuit being outside a coupling of the RF power source to the first region, where the first coupling circuit is configured to adjust a power distribution of the first region. The second region includes a second antenna.